

ABSTRACT

A semiconductor device according to the present disclosure has a dolmen structure including a substrate, a first chip disposed on the substrate, a plurality of support pieces disposed around the first chip, on
5 the substrate, and a second chip disposed to be supported by the plurality of support pieces and to cover the first chip, in which the support piece contains a cured product of a thermosetting resin composition, or includes a layer containing a cured product of a thermosetting resin composition, and a resin layer or a metal layer.

Fig. 1